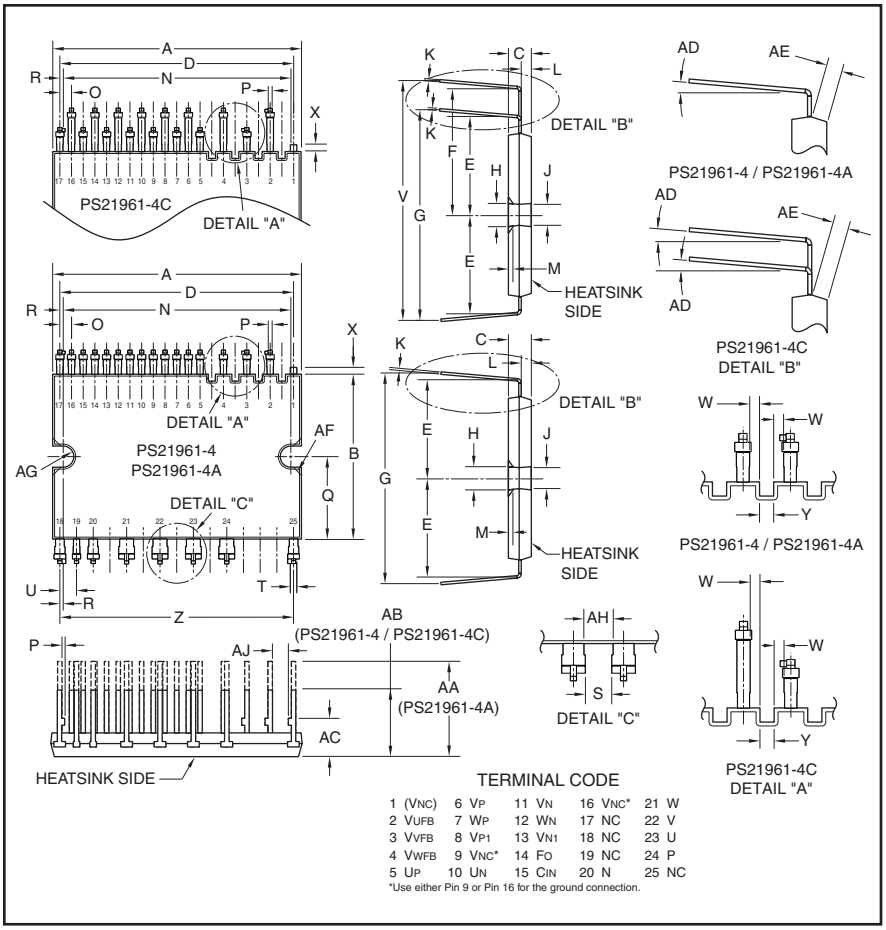
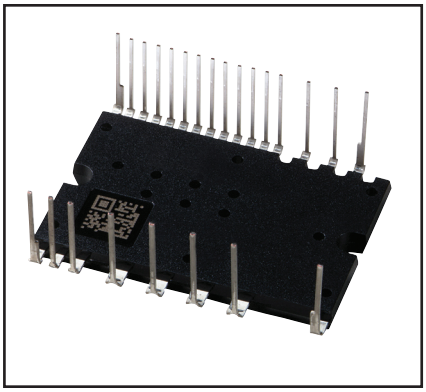
PS21961-4, PS21961-4A, PS21961-4C

Powerex, Inc., 173 Pavilion Lane, Youngwood, Pennsylvania 15697-1800 (724) 925-7272

Intellimod™ Module

Dual-In-Line Intelligent Power Module
3 Amperes/600 Volts





Description:
DIP-IPMs are intelligent power modules that integrate power devices, drivers, and protection circuitry in an ultra compact dual-in-line transfer-mold package for use in driving small three phase motors. Use of 5th generation IGBTs, DIP packaging, and application specific HVICs allow the designer to reduce inverter size and overall design time.

Features:
- ☐ Compact Packages
- ☐ Single Power Supply
- ☐ Integrated HVICs
- ☐ Direct Connection to CPU
- ☐ Reduced R_{th}

Applications:
- ☐ Refrigerators
- ☐ Air Conditioners
- ☐ Small Servo Motors
- ☐ Small Motor Control

Ordering Information:
PS21961-4 is a 600V, 3 Ampere short pin DIP Intelligent Power Module.

PS21961-4A – long pin type
PS21961-4C – zigzag pin type

Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	1.50±0.02	38.0±0.5
B	0.94±0.02	24.0±0.5
C	0.14	3.5
D	1.40	35.56
E	0.57±0.02	14.4±0.5
F	0.74±0.02	18.9±0.5
G	1.15±0.02	29.2±0.5
H	0.14	3.5
J	0.13	3.3
K	0.016	0.4
L	0.06±0.02	1.5±0.05
M	0.031	0.8
N	1.39±0.019	35.0±0.3
O	0.07±0.008	1.778±0.2
P	0.02	0.5
Q	0.47	12.0
R	0.011	0.28

Dimensions	Inches	Millimeters
S	0.12	2.8
T	0.024	0.6
U	0.1±0.008	2.54±0.2
V	1.33±0.02	33.7±0.5
W	0.03	0.678
X	0.04	1.0
Y	0.05	1.2
Z	1.40	35.56
AA	0.55±0.02	14.0±0.5
AB	0.37±0.02	9.5±0.5
AC	0.22±0.02	5.5±0.5
AD	0 ~ 5°	0 ~ 5°
AE	0.06 Min.	1.5 Min.
AF	0.05	1.2
AG	0.063 Rad.	1.6 Rad.
AH	0.118 Min.	3.0 Min.
AJ	0.098 Min.	2.5 Min.

PS21961-4, PS21961-4A, PS21961-4C
Intellimod™ Module
Dual-In-Line Intelligent Power Module
3 Amperes/600 Volts

Absolute Maximum Ratings, T_j = 25°C unless otherwise specified

Characteristics	Symbol	PS21961-4, PS21961-4A PS21961-4C	Units
Power Device Junction Temperature*	T_j	-20 to 125	°C
Storage Temperature	T_{stg}	-40 to 125	°C
Case Operating Temperature (Note 1)	T_C	-20 to 100	°C
Mounting Torque, M3 Mounting Screws	—	6.9	in-lb
Module Weight (Typical)	—	10	Grams
Heatsink Flatness (Note 2)	—	-50 to 100	µm
Self-protection Supply Voltage Limit (Short Circuit Protection Capability)**	$V_{CC(prot.)}$	400	Volts
Isolation Voltage, AC 1 minute, 60Hz Sinusoidal, Connection Pins to Heatsink Plate	V_{ISO}	1500	Volts

*The ma ximum junction temperature rating of the power chips integrated within the DIP-IPM is 150°C (@$T_C \leq$ 100°C). However, to ensure safe operation of the DIP-IPM, the average junction temperature should be limited to $T_{j(avg)} \leq$125°C (@$T_C \leq$ 100°C).

**V_D = 13.5 ~ 16.5V, Inverter Part, T_j = 125°C, Non-repetitive, Less than 2µs

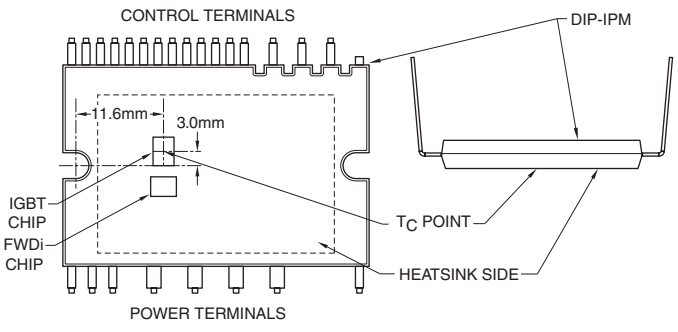
IGBT Inverter Sector

Collector-Emitter Voltage	V_{CES}	600	Volts
Each Collector Current, ± (T_C = 25°C)	I_C	3	Amperes
Each Peak Collector Current, ± (T_C = 25°C, Less than 1ms)	I_{CP}	6	Amperes
Supply Voltage (Applied between P - N)	V_{CC}	450	Volts
Supply Voltage, Surge (Applied between P - N)	$V_{CC(surge)}$	500	Volts
Collector Dissipation (T_C = 25°C, per 1 Chip)	P_C	21.3	Watts

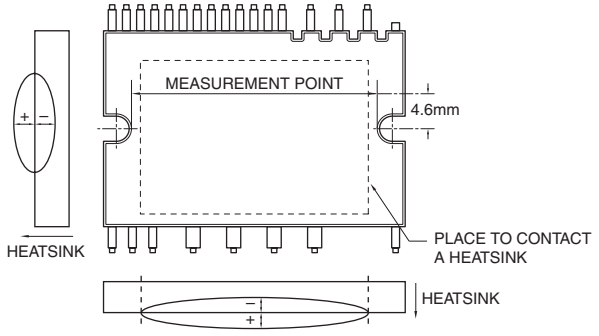
Control Sector

Supply Voltage (Applied between V_{P1}-V_{NC}, V_{N1}-V_{NC})	V_D	20	Volts
Supply Voltage (Applied between V_{UFB}-U, V_{VFB}-V, V_{WFB}-W)	V_{DB}	20	Volts
Input Voltage (Applied between U_P, V_P, W_P-V_{NC}, U_N, V_N, W_N-V_{NC})	V_{IN}	-0.5 ~ V_D+0.5	Volts
Fault Output Supply Voltage (Applied between F_O-V_{NC})	V_{FO}	-0.5 ~ V_D+0.5	Volts
Fault Output Current (Sink Current at F_O Terminal)	I_{FO}	1	mA
Current Sensing Input Voltage (Applied between C_{IN}-V_{NC})	V_{SC}	-0.5 ~ V_D+0.5	Volts

Note 1 – T_C Measure Point



Note 2 – Flatness Measurement Position



Electrical and Mechanical Characteristics, T_j = 25°C unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
IGBT Inverter Sector						
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_D = V_{DB}$ = 15V, I_C = 3A, V_{IN} = 5V, T_j = 25°C	—	1.60	2.15	Volts
		$V_D = V_{DB}$ = 15V, I_C = 3A, V_{IN} = 5V, T_j = 125°C	—	1.70	2.30	Volts
Diode Forward Voltage	V_{EC}	$-I_C$ = 3A, V_{IN} = 0V	—	1.55	2.10	Volts
Inductive Load Switching Times	t_{on}	V_{CC} = 300V,	0.50	0.95	1.50	µs
	t_{rr}	$V_D = V_{DB}$ = 15V,	—	0.30	—	µs
	$t_{C(on)}$	I_C = 3A, T_j = 125°C,	—	0.35	0.55	µs
	t_{off}	V_{IN} = 0 ⇔ 5V,	—	1.40	2.00	µs
	$t_{C(off)}$	Inductive Load	—	0.50	0.80	µs
Collector Cutoff Current	I_{CES}	$V_{CE} = V_{CES}$, T_j = 25°C	—	—	1.0	mA
		$V_{CE} = V_{CES}$, T_j = 125°C	—	—	10	mA
Control Sector						
Circuit Current I_D	V_{IN} = 5V	Total of V_{P1}-V_{NC}, V_{N1}-V_{NC}	—	—	2.80	mA
$V_D = V_{DB}$ = 15V		V_{UFB}-U, V_{VFB}-V, V_{WFB}-W	—	—	0.55	mA
	V_{IN} = 0V	Total of V_{P1}-V_{NC}, V_{N1}-V_{NC}	—	—	2.80	mA
		V_{UFB}-U, V_{VFB}-V, V_{WFB}-W	—	—	0.55	mA
Fault Output Voltage	V_{FOH}	V_{SC} = 0V, F_O Terminal Pull-up to 5V by 10kΩ	4.9	—	—	Volts
	V_{FOL}	V_{SC} = 1V, I_{FO} = 1mA	—	—	0.95	Volts
Input Current	I_{IN}	V_{IN} = 5V	0.70	1.00	1.50	mA
Short Circuit Trip Level*	$V_{SC(ref)}$	V_D = 15V*	0.43	0.48	0.53	Volts
Supply Circuit Under-voltage	UV_{DBt}	Trip Level, $T_j \leq$ 125°C	10.0	—	12.0	Volts
	UV_{DBr}	Reset Level, $T_j \leq$ 125°C	10.5	—	12.5	Volts
	UV_{Dt}	Trip Level, $T_j \leq$ 125°C	10.3	—	12.5	Volts
	UV_{Dr}	Reset Level, $T_j \leq$ 125°C	10.8	—	13.0	Volts
Fault Output Pulse Width**	t_{FO}		20	—	—	µs
ON Threshold Voltage	$V_{th(on)}$	Applied between	—	2.1	2.6	Volts
OFF Threshold Voltage	$V_{th(off)}$	U_P, V_P, W_P-V_{NC},	0.8	1.3	—	Volts
ON/OFF Threshold Hysteresis Voltage	$V_{th(hys)}$	U_N, V_N, W_N-V_{NC}	0.35	0.65	—	Volts

* Short Circuit protection is functioning only for the low-arms. Please select the value of the external shunt resistor such that the S_C trip level is less than 1.7 times the current rating.
**Fault signal is asserted only for a U_V or S_C condition on the low side. On a S_C fault the F_O duration will be 20µsec. On a U_V condition the fault signal will be asserted as long as the U_V condition exists or for 20µsec, whichever is longer.

Thermal Characteristics

Characteristic	Symbol	Condition	Min.	Typ.	Max.	Units
Junction to Case	$R_{th(j-c)Q}$	Inverter RC-IGBT (Per 1/6 Module)	—	—	4.7	°C/Watt

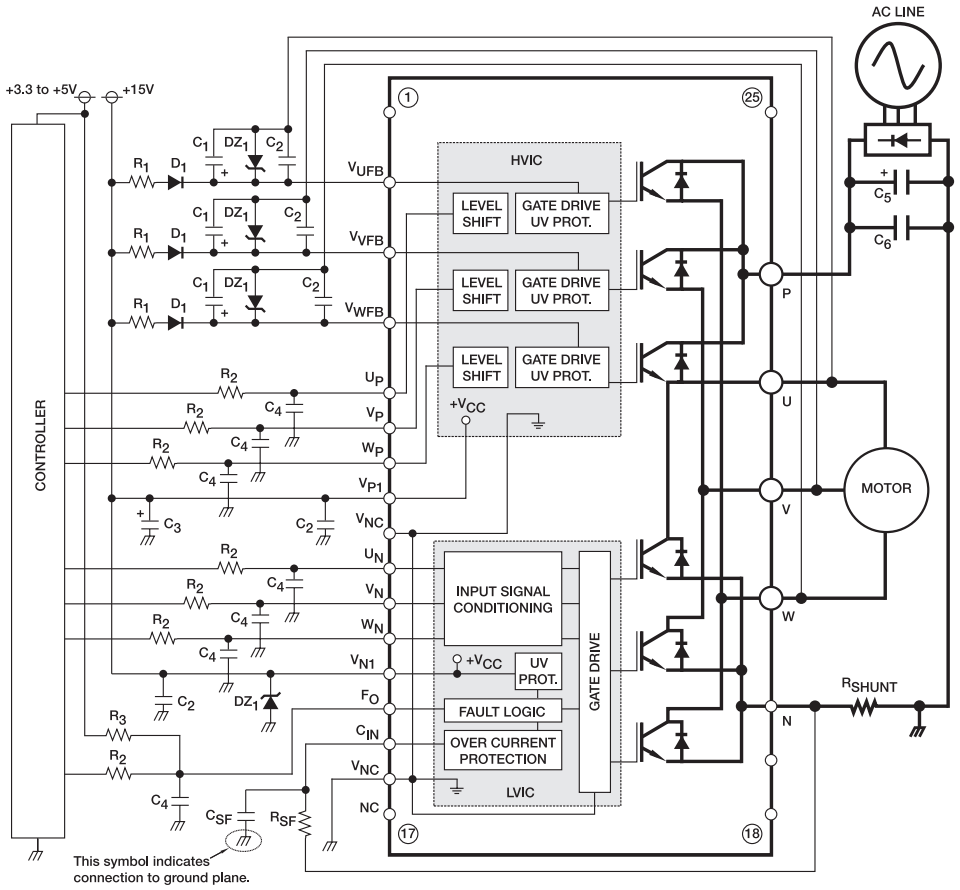
Recommended Conditions for Use

Characteristic	Symbol	Condition	Min.	Typ.	Value	Units
Supply Voltage	V_{CC}	Applied between P-N Terminals	0	300	400	Volts
Control Supply Voltage	V_D	Applied between V_{P1}-V_{NC}, V_{N1}-V_{NC}	13.5	15.0	16.5	Volts
	V_{DB}	Applied between V_{UFB}-U, V_{VFB}-V, V_{WFB}-W	13.0	15.0	18.5	Volts
Control Supply Variation	dV_D, dV_{DB}		-1	—	1	V/µs
Arm Shoot-through Blocking Time	t_{DEAD}	For Each Input Signal, $T_C \leq 100°C$	1.5	—	—	µs
Allowable Minimum Input	$P_{WIN(on)}$		0.5	—	—	µs
Pulse Width*	$P_{WIN(off)}$		0.5	—	—	µs
V_{NC} Voltage Variation	V_{NC}	Between V_{NC}-N (Including Surge)	-5.0	—	5.0	Volts

*DIP-IPM might not make response or work properly if the input signal plus width is less than the recommended minimum value.

PS21961-4, PS21961-4A, PS21961-4C
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Application Circuit



Component Selection:

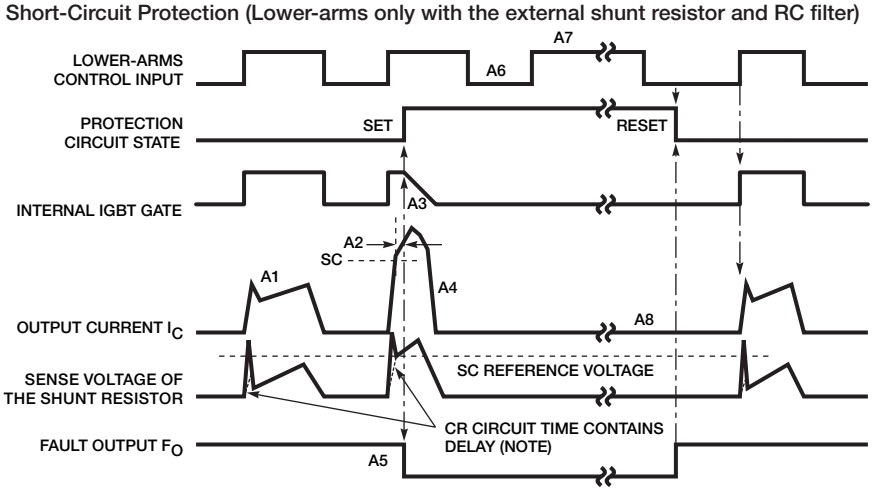
Dsgn.	Typ. Value	Description
D_1	1A, 600V	Boot strap supply diode – Ultra fast recovery
DZ_1	24V, 1.0W	Control and boot strap supply over voltage suppression
C_1	10-100uF, 50V	Boot strap supply reservoir – Electrolytic, long life, low Impedance, 105°C (Note 5)
C_2	0.22-2.0uF, 50V	Local decoupling/High frequency noise filters – Multilayer ceramic (Note 8)
C_3	10-100uF, 50V	Control power supply filter – Electrolytic, long life, low Impedance, 105°C
C_4	100pF, 50V	Optional Input signal noise filter – Multilayer ceramic (Note 1)
C_5	200-2000uF, 450V	Main DC bus filter capacitor – Electrolytic, long life, high ripple current, 105°C
C_6	0.1-0.22uF, 450V	Surge voltage suppression capacitor – Polyester/Polypropylene film (Note 9)
C_{SF}	1000pF, 50V	Short circuit detection filter capacitor – Multilayer Ceramic (Note 6, Note 7)
R_{SF}	1.8k ohm	Short circuit detection filter resistor (Note 6, Note 7)
R_{SHUNT}	5-100mohm	Current sensing resistor – Non-inductive, temperature stable, tight tolerance (Note 10)
R_1	10 ohm	Boot strap supply inrush limiting resistor (Note 5)
R_2	330 ohm	Optional control input noise filter (Note 1, Note 2)
R_3	10k ohm	Fault output signal pull-up resistor (Note 3)

Notes:

1) To prevent input signal oscillations minimize wiring length to controller (~2cm). Additional RC filtering (C5 etc.) may be required. If filtering is added be careful to maintain proper dead time and voltage levels. See application notes for details.
2) Internal HVIC provides high voltage level shifting allowing direct connection of all six driving signals to the controller.
3) F_O output is an open collector type. Pull up resistor (R3) should be adjusted to current sink capability of the controller.
4) Use only one V_{NC} Pin (either 9 or 16) and leave the other open.
5) Boot strap supply component values must be adjusted depending on the PWM frequency and technique.
6) Wiring length associated with R_{SHUNT}, R_{SF}, C_{SF} must be minimized to avoid improper operation of the OC function.
7) R_{SF}, C_{SF} set over current protection trip time. Recommend time constant is 1.5µs-2.0µs. See application notes.
8) Local decoupling/high frequency filter capacitors must be connected as close as possible to the modules pins.
9) The length of the DC link wiring between C5, C6, the DIP's P terminal and the shunt must be minimized to prevent excessive transient voltages. In particular C6 should be mounted as close to the DIP as possible.
10) Use high quality, tight tolerance current sensing resistor. Connect resistor as close as possible to the DIP's N terminal. Be careful to check for proper power rating. See application notes for calculation of resistance value.

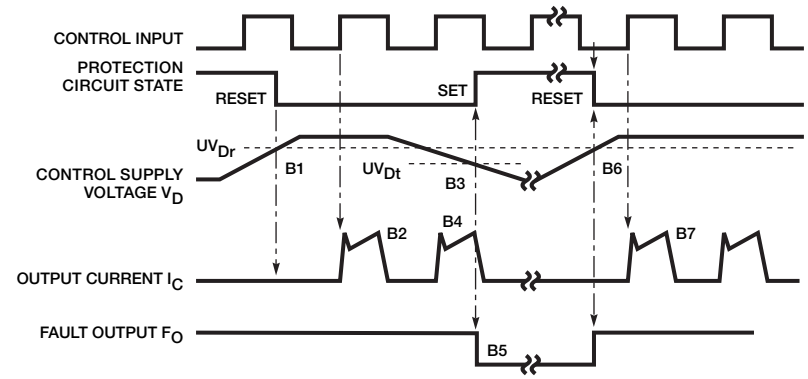
Protection Function Timing Diagrams

Short-Circuit Protection (Lower-arms only with the external shunt resistor and RC filter)



A1: Normal operation – IGBT turn on and conducting current.
A2: Short-circuit current detected (SC trigger).
A3: IGBT gate hard interrupted.
A4: IGBT turn off.
A5: F_O output with a fixed pulse width of $t_{FO(min)}$ = 20µs.
A6: Input "L" – IGBT off.
A7: Input "H" – IGBT on is blocked during the F_O output period.
A8: IGBT stays in off state.

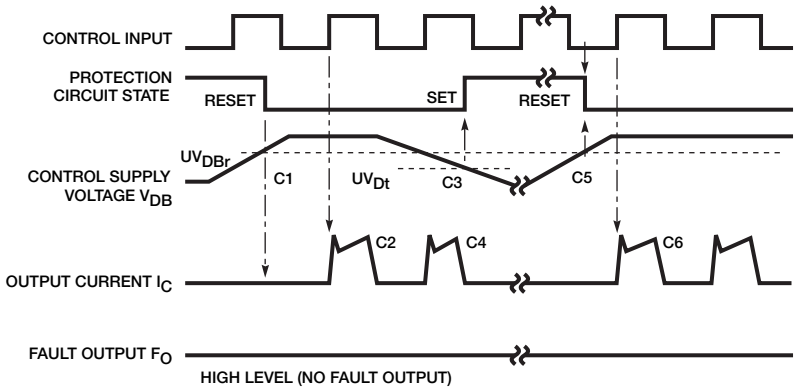
Under-Voltage Protection (Lower-side, UV_D)



B1: Control supply voltage rise – After the voltage level reaches UV_{Dr}, the drive circuit begins to work at the rising edge of the next input signal.
B2 : Normal operation – IGBT turn on and conducting current.
B3: Under-voltage trip (UV_{Dt}).
B4: IGBT turn off regardless of the control input level.
B5: F_O output during under-voltage period, however, the minimum pulse width is 20µs.
B6: Under-voltage reset (UV_{Dr}).
B7: Normal operation – IGBT turn on and conducting current.

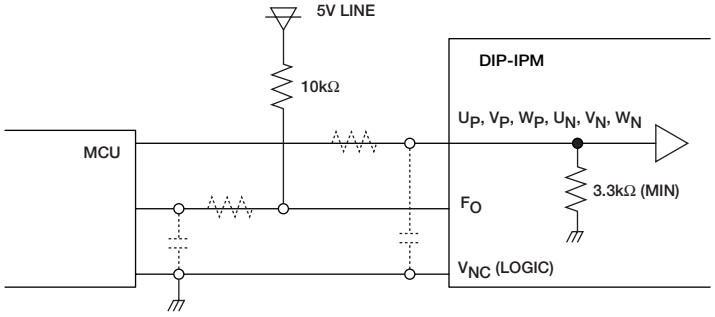
Protection Function Timing Diagrams

Under-Voltage Protection (Upper-side, UV_{DB})



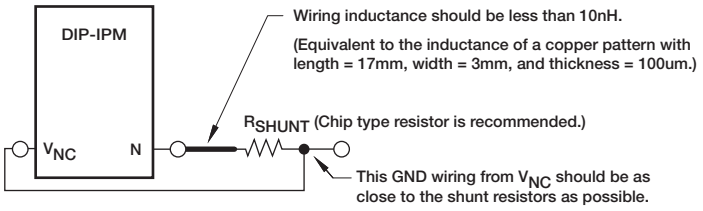
C1: Control supply voltage rises – After the voltage level reaches UV_{DBr}, the drive circuit begins to work at the rising edge of the next input signal.
C2: Normal operation – IGBT turn on and conducting current.
C3: Under-voltage trip (UV_{DBt}).
C4: IGBT stays off regardless of the control input level, but there is no F_O signal output.
C5: Under-voltage reset (UV_{Dr}).
C6: Normal operation – IGBT turn on and conducting current.

Typical Interface Circuit



NOTE: RC coupling at each input (parts shown dotted) may change depending on the PWM control scheme used in the application and the wiring impedance of the printed circuit board. The DIP-IPM input signal section integrates a 3.3kΩ (min) pull-down resistor. Therefore, when using an external filtering resistor, care must be taken to satisfy the turn-on threshold voltage requirement.

Wiring Method Around Shunt Resistor



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